

A method for single-crystals of silicon production with necessary carbon content includes definition of concentration of carbon atoms on the butt-end of the crystal, cutting off from its butt-end of the part with increased carbon content, repeat determination of the concentration of carbon atoms on the butt-end of the ingot. The length of single-crystal part with increased carbon content is calculated according to formula. The proposed method allows to produce the single-crystals of silicon with possible carbon content with efficiency not less than 90 %, which is within the range of the set measurement accuracy for this method of determination of carbon concentration.